

N-CHANNEL ENHANCEMENT MOS FET

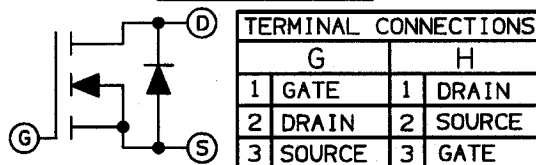
1000V, 9A, 1.4 Ω

SDF9N100 JEA
SDF9N100 JEB
SDF9N100 JEC
SDF9N100 JED

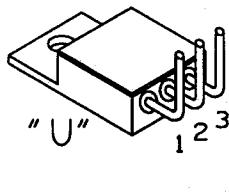
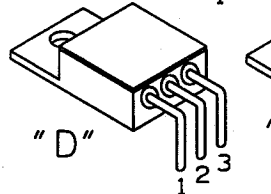
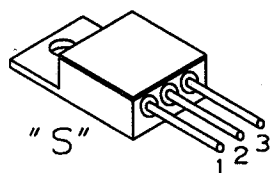
FEATURES

- RUGGED PACKAGE
- HI-REL CONSTRUCTION
- CERAMIC EYELETS
- LEAD BENDING OPTIONS
- COPPER CORED 52 ALLOY PINS
- LOW IR LOSSES
- LOW THERMAL RESISTANCE
- OPTIONAL MIL-S-19500 SCREENING

SCHEMATIC



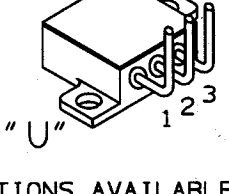
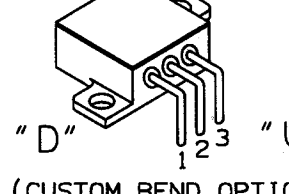
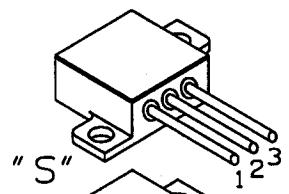
STANDARD BEND CONFIGURATIONS



(CUSTOM BEND OPTIONS AVAILABLE)

JEA
JEC

STANDARD BEND CONFIGURATIONS



(CUSTOM BEND OPTIONS AVAILABLE)

JEB
JED

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL		UNITS
Drain-source Volt.(1)	VDSS	1000	Vdc
Drain-Gate Voltage (Rgs=1.0M Ω) (1)	VDGR	1000	Vdc
Gate-Source Voltage Continuous	VGS	± 20	Vdc
Drain Current Continuous (Tc = 25°C)	ID	9	Adc
Drain Current Pulsed(3)	IDM	36	A
Total Power Dissipation	PD	300	W
Power Dissipation Derating > 25°C		2.4	W/°C
Operating & Storage Temp.	TJ/Tsig	-55 TO +150	°C
Thermal Resistance	RthJc	0.42	°C/W
Max.Lead temperature	TL	300	°C

ELECTRICAL CHARACTERISTICS Tc = 25°C (UNLESS OTHERWISE SPECIFIED)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain-source Breakdown Volt.	V(BR)DSS	VGS=0V ID=250 μ A	1000	-	-	V
Gate Threshold Voltage	VGS(TH)	VDS=VGS ID=250 μ A	2.0	-	4.5	V
Gate Source Leakage	IGSS	VGS= ± 20 V	-	-	100	nA
Zero Gate Voltage Drain Current	IDSS	VDS=MAX.RATING VGS=0 VDS=0.8 MAX.RATING VGS=0 TJ=125°C	-	-	250 1000	μ A
Static Drain-Source On-State Resistance(1)	RDS(ON)	VGS=10 V ID=4.5A	-	-	1.4	Ω
Forward Trans-Conductance (2)	gfs	VDS $\geq$ 50 V IDS=4.5A	6.0	-	-	S(U)
Input Capacitance	CISS	VGS=0V VDS=25 V f=1.0 MHz	-	4500	-	pF
Output Capacitance	COSS		-	550	-	pF
Reverse Transfer Capacitance	CRSS		-	160	-	pF
Turn-On Delay	td(on)	VDD=500V Zo=50n ID=4.5A	-	-	100	ns
Rise Time	tr		-	-	110	ns
Turn-Off Delay	td(off)	(MOSFET switching times are essentially independent of operating temp.)	-	-	220	ns
Fall Time	tf		-	-	105	ns
Total Gate Charge (Gate-Source Plus Gate-Drain)	Qg	VGS=10V, ID=9A	-	145	-	nC
Gate-Source Charge	Qgs	VDS=0.8 MAX.RATING (Gate charge is essentially independent of the operating temperature)	-	55	-	nC
Gate-Drain ("Miller") Charge	Qgd		-	90	-	nC

SOURCE-DRAIN DIODE RATINGS & CHARACT. Tc = 25°C (UNLESS OTHERWISE SPECIFIED)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Continuous Source Current (Body Diode)	IS	Modified MOSFET symbol showing the integral reverse P-N junction rectifier (See schematic)	-	-	9	A
Pulse Source Current (Body Diode) (1)	ISM		-	-	36	A
Diode Forward Voltage (2)	VSD	IF=9A VGS=0V Tc=+25°C	-	-	1.5	V
Reverse Recovery Time	trr	Tc=+25° C IF=9A	-	600	-	ns
Reverse Recovery Charge	Qrr	di/dt=100A/ μ S	-	8.5	-	μ C

REL.3/93

(1) TJ = 25°C to 150°C.
(2) Pulse test: Pulse Width < 300 μ S, Duty Cycle < 2%
(3) Repetitive Rating: Pulse Width limited By Max.junction Temperature.